Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low leakage current
- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.0 × 0.6 × 0.48 mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R_{DSon} = 1.02 Ω

3. Applications

- Relay driver
- · High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-500	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -500 \text{ mA}; T_j = 25 \text{ °C}$		-	1.02	1.4	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D I
2	S	source	2 🔲 📗 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S S 017aaa259

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZ950UPEL	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883		

6. Marking

Table 4. Marking codes

Type number	Marking code
PMZ950UPEL	L2

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-500	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-300	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	2700	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
Is	source current	T _{amb} = 25 °C	[1]	-	-350	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

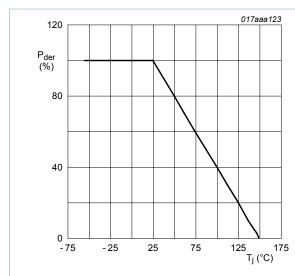


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

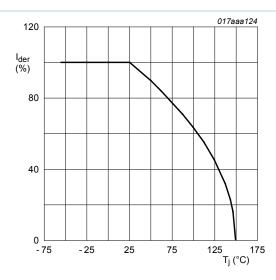


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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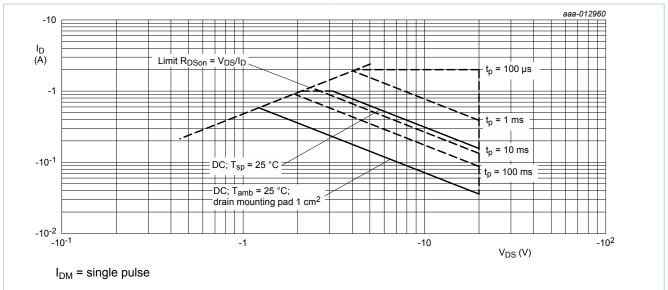


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

8. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	305	360	K/W
from junction to ambient			[2]	-	150	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	40	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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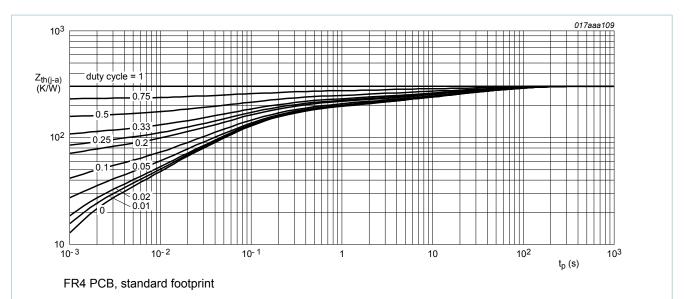


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

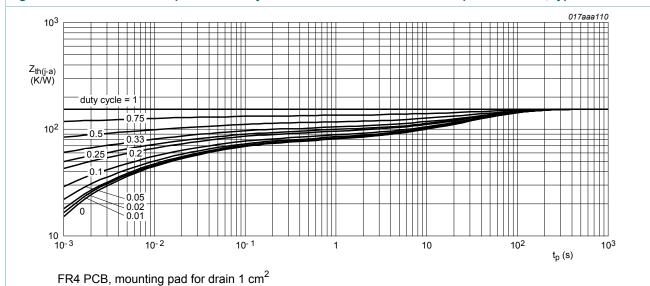


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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9. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μΑ
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μA
		V _{DS} = -5 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-25	nA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = 1.8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	50	nA
	V_{GS} = -1.8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-50	nA	
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -500 mA; T_j = 25 °C	-	1.02	1.4	Ω
	resistance	V_{GS} = -4.5 V; I_D = -500 mA; T_j = 150 °C	-	1.54	2.1	Ω
		V_{GS} = -2.5 V; I_D = -200 mA; T_j = 25 °C	-	1.27	2.2	Ω
		V_{GS} = -1.8 V; I_{D} = -40 mA; T_{j} = 25 °C	-	1.7	3.3	Ω
		V_{GS} = -1.5 V; I_{D} = -10 mA; T_{j} = 25 °C	-	2.3	5	Ω
		V_{GS} = -1.2 V; I_{D} = -1 mA; T_{j} = 25 °C	-	3.5	-	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -500 mA; T_j = 25 °C	-	480	-	mS
Dynamic ch	naracteristics					,
$Q_{G(tot)}$	total gate charge	$V_{DS} = -10 \text{ V}; I_{D} = -450 \text{ mA};$	-	1.19	2.1	nC
Q_{GS}	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.17	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	43	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	14	-	pF
C _{rss}	reverse transfer capacitance		-	8	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -0.45 A; R_{L} = 22 Ω ;	-	2.3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	13.5	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _f	fall time			-	6	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_S = -115 mA; V_{GS} = 0 V; T_j = 25 °C		-	-0.7	-1.2	V

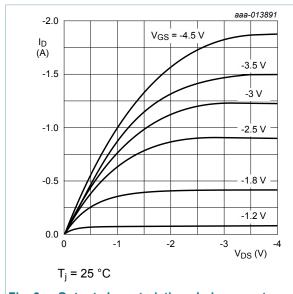


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

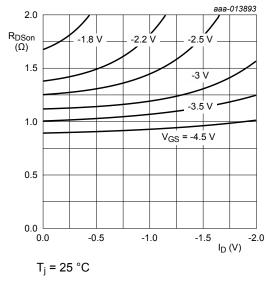


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

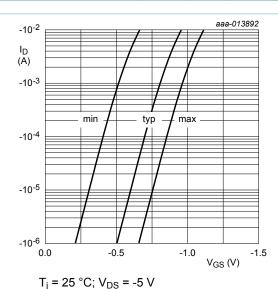


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

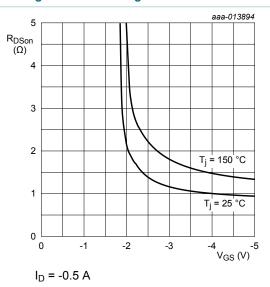


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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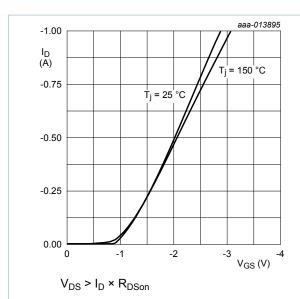


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

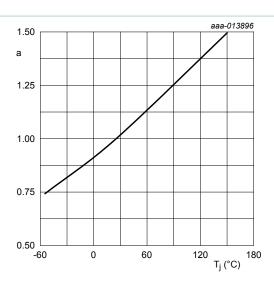


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

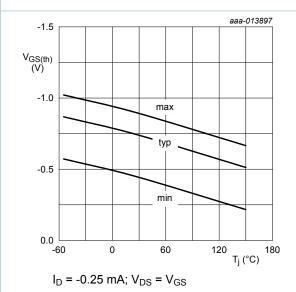


Fig. 12. Gate-source threshold voltage as a function of junction temperature

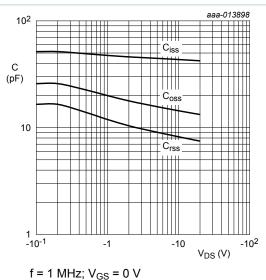


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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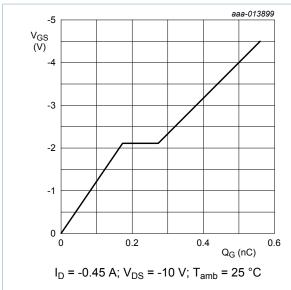


Fig. 14. Gate-source voltage as a function of gate charge; typical values

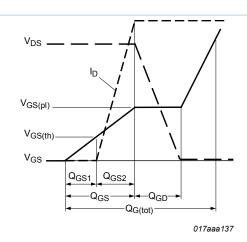


Fig. 15. MOSFET transistor: Gate charge waveform definitions

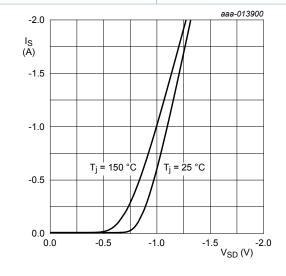
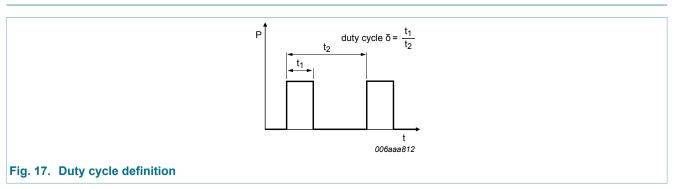


Fig. 16. Source current as a function of source-drain voltage; typical values

10. Test information

 $V_{GS} = 0 V$



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11. Package outline

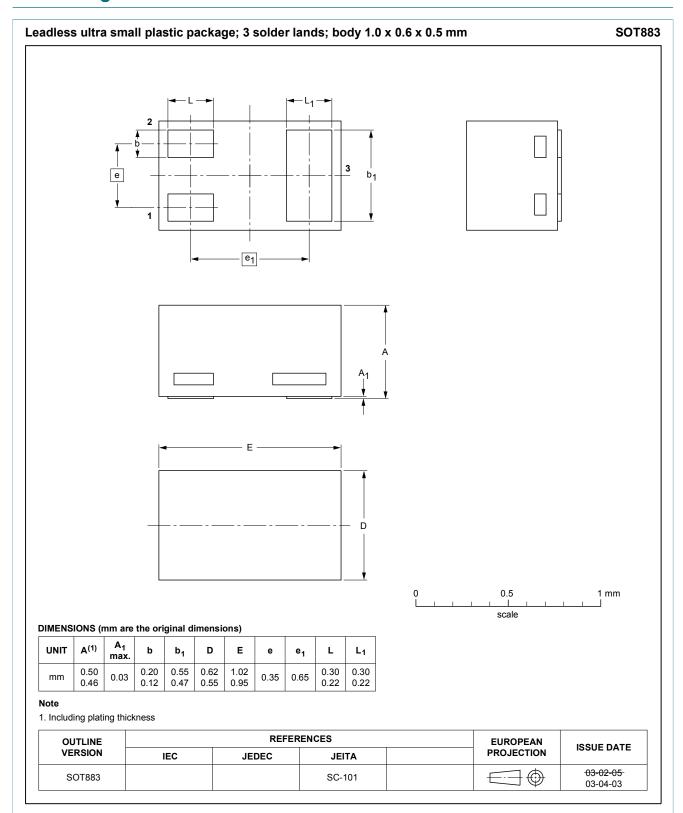


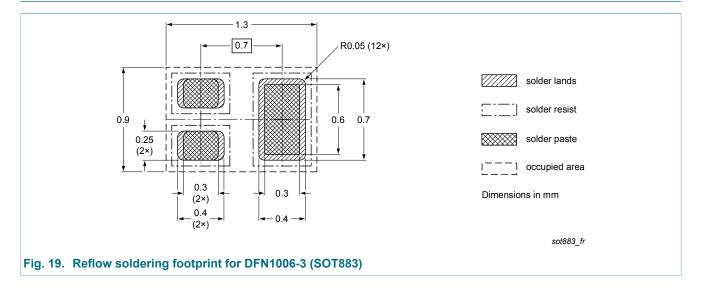
Fig. 18. Package outline DFN1006-3 (SOT883)

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12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ950UPEL v.1	20160628	Product data sheet	-	-

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14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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